Document Title

1Mx4 Bit High Speed Static RAM(5V Operating).
Operated at Extended and Industrial Temperature Ranges.

Revision History

RevNo.	History	Draft Data	Remark
Rev. 0.0	Initial release with Preliminary.	Feb. 12. 1999	Preliminary
Rev. 1.0	1.1 Removed Low power Version. 1.2 Removed Data Retention Characteristics 1.3 Changed I_{SB1} to 20mA	Mar. 29. 1999	Preliminary
Rev. 2.0	2.1 Relax D.C parameters.	Aug. 19. 1999	Preliminary

Item		Previous	Current
I_{CC}	12ns	160mA	190mA
	15ns	155mA	185mA
	20ns	150mA	180mA

2.2 Relax Absolute Maximum Rating.

Item	Previous	Current
Voltage on Any Pin Relative to Vss	-0.5 to 7.0	-0.5 to Vcc+0.5

RevNo.	History	Draft Data	Remark
Rev. 3.0	3.1 Delete Preliminary	Mar. 27. 2000	Final

3.2 Update D.C parameters and 10ns part.

	Previous			Current		
	I_{CC}	I_{sb}	I_{sb1}	I_{CC}	I_{sb}	I_{sb1}
10ns	-			160mA		
12ns	190mA	70mA	20mA	150mA	60mA	10mA
15ns	185mA			140mA		
20ns	180mA			130mA		

3.3 Added Extended temperature range

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K6R4004C1C-C, K6R4004C1C-I, K6R4004C1C-E   CMOS SRAM

1M x 4 Bit (with OE)High-Speed CMOS Static RAM

### FEATURES

• Fast Access Time 10,12,15,20ns(Max.)
• Low Power Dissipation
   Standby (TTL)   : 60mA(Max.)
              (CMOS) : 10mA(Max.)
   Operating   K6R4004C1C-10 : 160mA(Max.)
                K6R4004C1C-12 : 150mA(Max.)
                K6R4004C1C-15 : 140mA(Max.)
                K6R4004C1C-20 : 130mA(Max.)
• Single 5.0V ±10% Power Supply
• TTL Compatible Inputs and Outputs
• I/O Compatible with 3.3V Device
• Fully Static Operation
   - No Clock or Refresh required
• Three State Outputs
• Center Power/Ground Pin Configuration
• Standard Pin Configuration
         K6R4004C1C-J : 32-SOJ-400

ORDERING INFORMATION

| K6R4004C1C-C10/C12/C15/C20	Commercial Temp.
K6R4004C1C-E10/E12/E15/E20	Extended Temp.
K6R4004C1C-I10/I12/I15/I20	Industrial Temp.

FUNCTIONAL BLOCK DIAGRAM
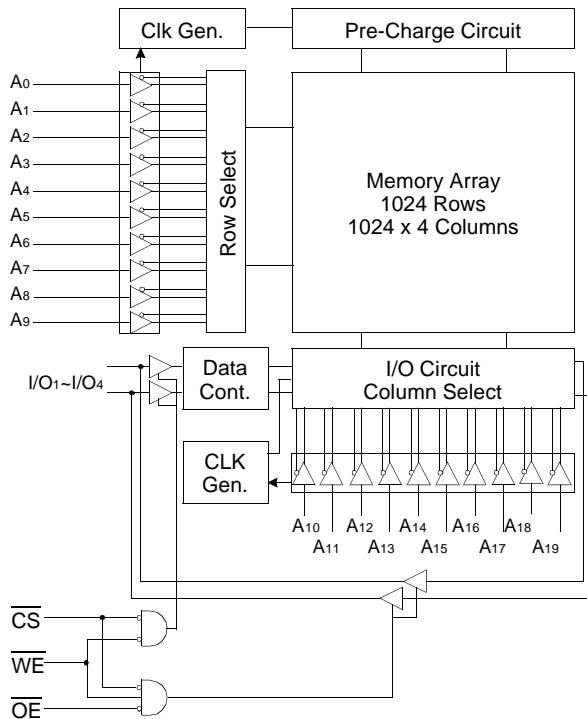
GENERAL DESCRIPTION

The K6R4004C1C is a 4,194,304-bit high-speed Static Random Access Memory organized as 1,048,576 words by 4 bits. The K6R4004C1C uses 4 common input and output lines and has an output enable pin which operates faster than address access time at read cycle. The device is fabricated using SAMSUNG's advanced CMOS process and designed for high-speed circuit technology. It is particularly well suited for use in high-density high-speed system applications. The K6R4004C1C is packaged in a 400 mil 32-pin plastic SOJ.

PIN CONFIGURATION(Top View)
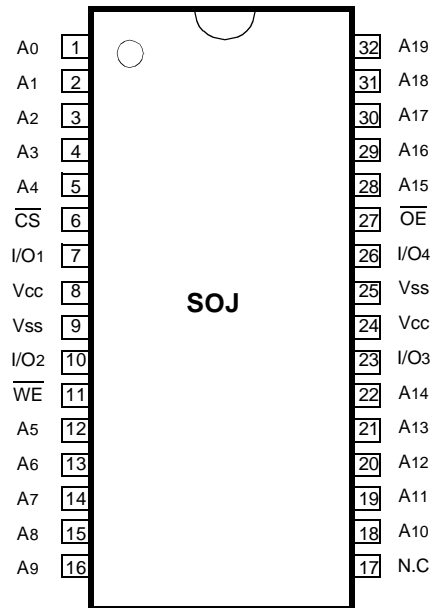
PIN FUNCTION

Pin Name	Pin Function
A0 - A19	Address Inputs
$\overline{WE}$	Write Enable
$\overline{CS}$	Chip Select
$\overline{OE}$	Output Enable
I/O1 ~ I/O4	Data Inputs/Outputs
Vcc	Power(+5.0V)
Vss	Ground
N.C	No Connection

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ABSOLUTE MAXIMUM RATINGS*

Parameter		Symbol	Rating	Unit
Voltage on Any Pin Relative to Vss		VIN, VOUT	-0.5 to Vcc+0.5	V
Voltage on Vcc Supply Relative to Vss		Vcc	-0.5 to 7.0	V
Power Dissipation		PD	1.0	W
Storage Temperature		TSTG	-65 to 150	°C
Operating Temperature	Commercial	TA	0 to 70	°C
	Extended	TA	-25 to 85	°C
	Industrial	TA	-40 to 85	°C

* Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS*(TA=0 to 70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	Vcc	4.5	5.0	5.5	V
Ground	Vss	0	0	0	V
Input High Voltage	VIH	2.2	-	Vcc+0.5***	V
Input Low Voltage	VIL	-0.5**	-	0.8	V

*   The above parameters are also guaranteed at extended and industrial temperature range.
**   VIL(Min) = -2.0V a.c(Pulse Width ≤ 8ns) for I ≤ 20mA.
*** VIH(Max) = Vcc + 2.0V a.c (Pulse Width ≤ 8ns) for I ≤ 20mA.

DC AND OPERATING CHARACTERISTICS*(TA=0 to 70°C, Vcc=5.0V±10%, unless otherwise specified)

Parameter	Symbol	Test Conditions			Min	Max	Unit
Input Leakage Current	ILI	VIN=Vss to Vcc			-2	2	μA
Output Leakage Current	ILO	CS=VIH or OE=VIH or WE=VIL VOUT=Vss to Vcc			-2	2	μA
Operating Current	ICC	Min. Cycle, 100% Duty CS=VIL, VIN=VIH or VIL, IOUT=0mA	Com.	10ns	-	160	mA
				12ns	-	150	
				15ns	-	140	
				20ns	-	130	
			Ext. Ind.	10ns	-	175	
				12ns	-	165	
				15ns	-	155	
				20ns	-	145	
Standby Current	ISB	Min. Cycle, CS=VIH			-	60	mA
	ISB1	f=0MHz, CS≥Vcc-0.2V, VIN≥Vcc-0.2V or VIN≤0.2V			-	10	
Output Low Voltage Level	VOL	IOL=8mA			-	0.4	V
Output High Voltage Level	VOH	IOH=-4mA			2.4	-	V
	VOH1**	IOH1=-0.1mA			-	3.95	V

* The above parameters are also guaranteed at extended and industrial temperature range.
** Vcc=5.0V±5%, Temp.=25°C.

CAPACITANCE*(TA=25°C, f=1.0MHz)

Item	Symbol	Test Conditions	MIN	Max	Unit
Input/Output Capacitance	CI/O	VI/O=0V	-	8	pF
Input Capacitance	CIN	VIN=0V	-	7	pF

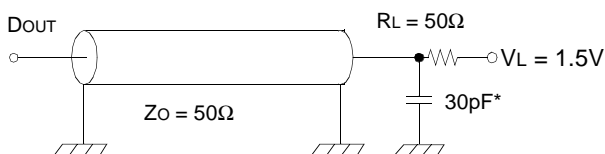* Capacitance is sampled and not 100% tested.

AC CHARACTERISTICS(TA=0 to 70°C, VCC=5.0V±10%, unless otherwise noted.)

TEST CONDITIONS*

Parameter	Value
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	3ns
Input and Output timing Reference Levels	1.5V
Output Loads	See below

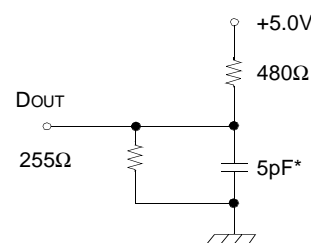* The above test conditions are also applied at extended and industrial temperature range.

Output Loads(A)

Output Loads(B)
for tHZ, tLZ, tWHZ, tOW, tOLZ & tOHZ

DOUT   RL = 50Ω

VL = 1.5V

ZO = 50Ω   30pF*

+5.0V

480Ω

DOUT

255Ω   5pF*

* Capacitive Load consists of all components of the
   test environment.

* Including Scope and Jig Capacitance

READ CYCLE*

Parameter	Symbol	K6R4004C1C-10		K6R4004C1C-12		K6R4004C1C-15		K6R4004C1C-20		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	tRC	10	-	12	-	15	-	20	-	ns
Address Access Time	tAA	-	10	-	12	-	15	-	20	ns
Chip Select to Output	tCO	-	10	-	12	-	15	-	20	ns
Output Enable to Valid Output	tOE	-	5	-	6	-	7	-	8	ns
Chip Enable to Low-Z Output	tLZ	3	-	3	-	3	-	3	-	ns
Output Enable to Low-Z Output	tOLZ	0	-	0	-	0	-	0	-	ns
Chip Disable to High-Z Output	tHZ	0	5	0	6	0	7	0	9	ns
Output Disable to High-Z Output	tOHZ	0	5	0	6	0	7	0	9	ns
Output Hold from Address Change	tOH	3	-	3	-	3	-	3	-	ns
Chip Selection to Power Up Time	tPU	0	-	0	-	0	-	0	-	ns
Chip Selection to Power DownTime	tPD	-	10	-	12	-	15	-	20	ns

* The above parameters are also guaranteed at extended and industrial temperature range.

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WRITE CYCLE*

| Parameter	Symbol	K6R4004C1C-10		K6R4004C1C-12		K6R4004C1C-15		K6R4004C1C-20		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t_{WC}	10	-	12	-	15	-	20	-	ns
Chip Select to End of Write	t_{CW}	7	-	8	-	10	-	12	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	0	-	ns
Address Valid to End of Write	t_{AW}	7	-	8	-	10	-	12	-	ns
Write Pulse Width($\overline{OE}$ High)	t_{WP}	7	-	8	-	10	-	12	-	ns
Write Pulse Width($\overline{OE}$ Low)	t_{WP1}	10	-	12	-	15	-	20	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	0	-	ns
Write to Output High-Z	t_{WHZ}	0	5	0	6	0	7	0	9	ns
Data to Write Time Overlap	t_{DW}	5	-	6	-	7	-	9	-	ns
Data Hold from Write Time	t_{DH}	0	-	0	-	0	-	0	-	ns
End Write to Output Low-Z	t_{OW}	3	-	3	-	3	-	3	-	ns

* The above parameters are also guaranteed at extended and industrial temperature range.

TIMMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{CS}=\overline{OE}=V_{IL}$, $\overline{WE}=V_{IH}$)
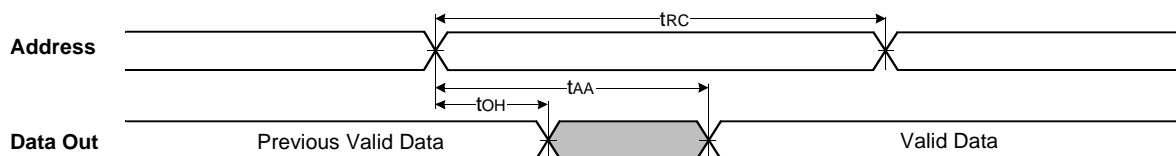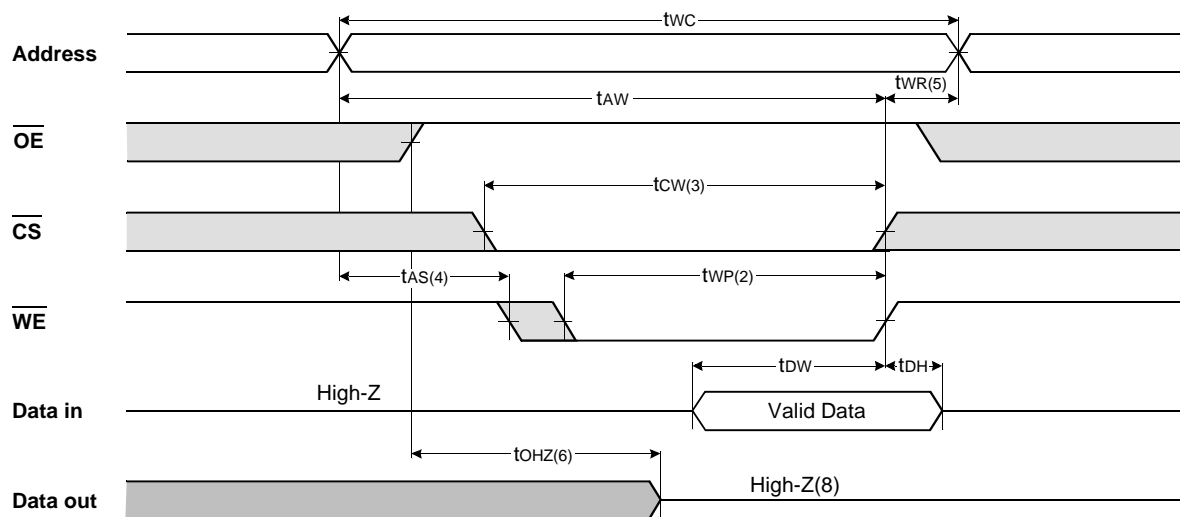

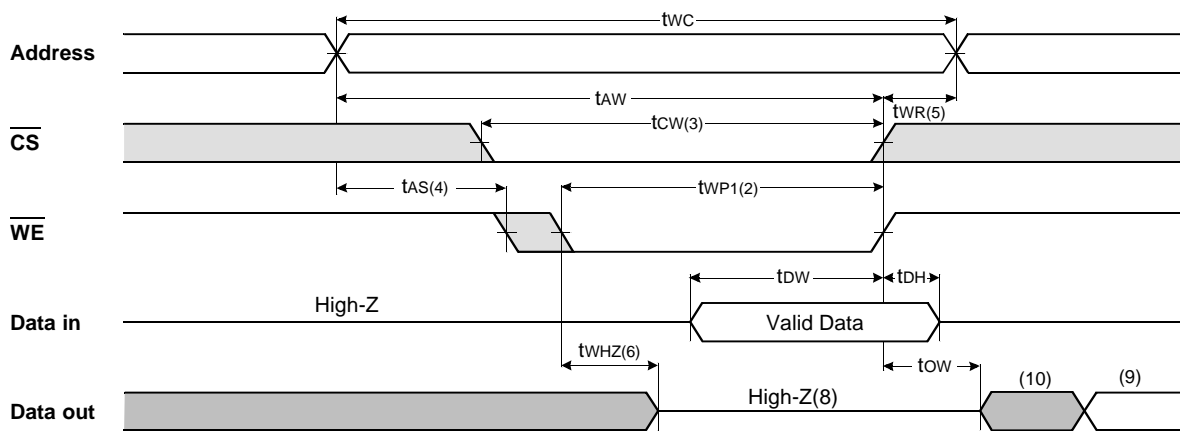### TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE}=V_{IH}$)
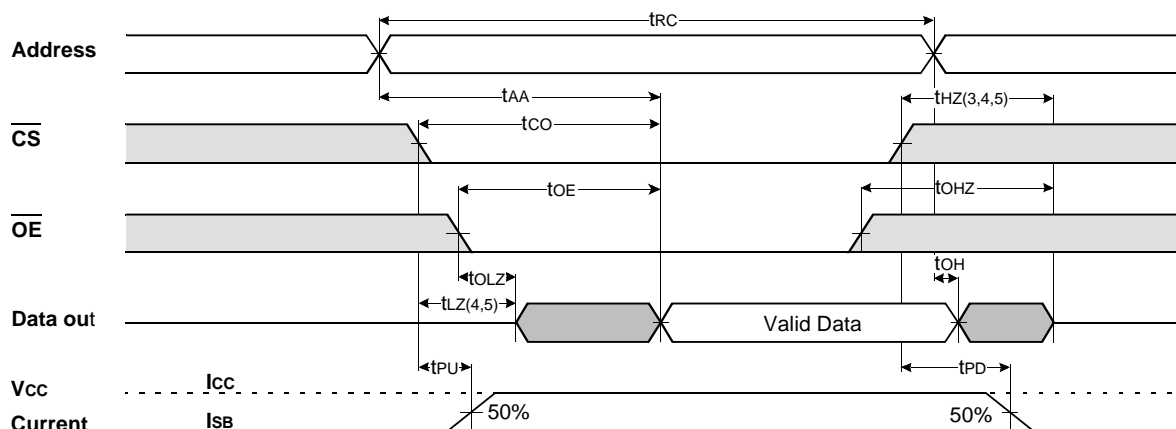
NOTES(READ CYCLE)

1. $\overline{WE}$ is high for read cycle.
2. All read cycle timing is referenced from the last valid address to the first transition address.
3. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit condition and are not referenced to V_{OH} or V_{OL} levels.
4. At any given temperature and voltage condition, t_{HZ}(Max.) is less than t_{LZ}(Min.) both for a given device and from device to device.
5. Transition is measured ±200mV from steady state voltage with Load(B). This parameter is sampled and not 100% tested.
6. Device is continuously selected with $\overline{CS}=V_{IL}$.
7. Address valid prior to coincident with $\overline{CS}$ transition low.
8. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.
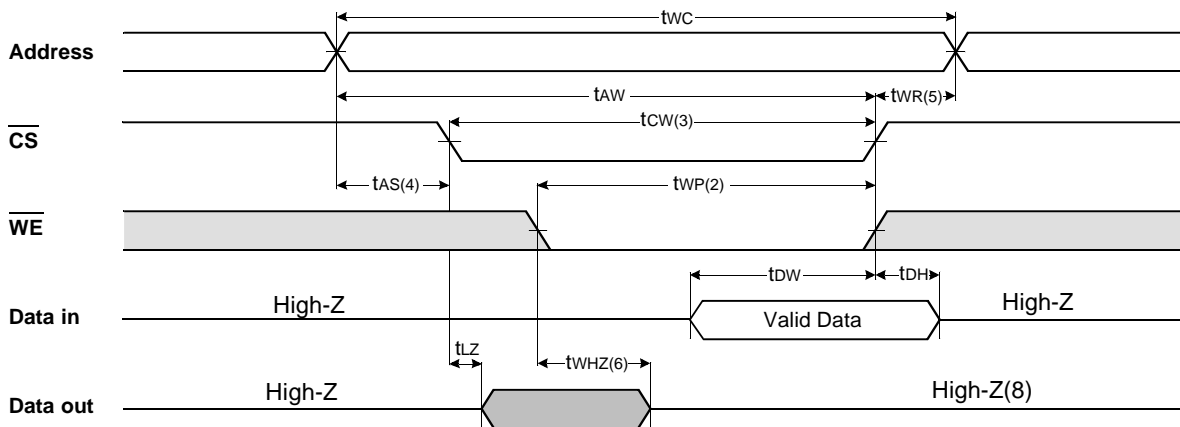
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TIMING WAVEFORM OF WRITE CYCLE(1) ($\overline{OE}$= Clock)

Address	t_{WC}
	t_{AW}
	$t_{WR(5)}$
$\overline{OE}$	
	$t_{CW(3)}$
$\overline{CS}$	
	$t_{AS(4)}$
	$t_{WP(2)}$
$\overline{WE}$	
	t_{DW} t_{DH}
Data in	High-Z Valid Data
	$t_{OHZ(6)}$
Data out	High-Z(8)

TIMING WAVEFORM OF WRITE CYCLE(2) ($\overline{OE}$=Low Fixed)

Address	t_{WC}
	t_{AW}
	$t_{CW(3)}$
	$t_{WR(5)}$
$\overline{CS}$	
	$t_{AS(4)}$
	$t_{WP1(2)}$
$\overline{WE}$	
	t_{DW} t_{DH}
Data in	High-Z Valid Data
	$t_{WHZ(6)}$ t_{OW} (10) (9)
Data out	High-Z(8)

TIMING WAVEFORM OF WRITE CYCLE(3) ($\overline{CS}$=Controlled)

Address	t_{WC}
	t_{AW}
	$t_{CW(3)}$
	$t_{WR(5)}$
$\overline{CS}$	
	$t_{AS(4)}$
	$t_{WP(2)}$
$\overline{WE}$	
	t_{DW} t_{DH}
Data in	High-Z Valid Data High-Z
	t_{LZ} $t_{WHZ(6)}$
Data out	High-Z High-Z(8)

NOTES(WRITE CYCLE)

1. All write cycle timing is referenced from the last valid address to the first transition address.
2. A write occurs during the overlap of a low $\overline{CS}$ and $\overline{WE}$. A write begins at the latest transition $\overline{CS}$ going low and $\overline{WE}$ going low ; A write ends at the earliest transition $\overline{CS}$ going high or $\overline{WE}$ going high. t_{WP} is measured from the beginning of write to the end of write.
3. t_{CW} is measured from the later of $\overline{CS}$ going low to end of write.
4. t_{AS} is measured from the address valid to the beginning of write.
5. t_{WR} is measured from the end of write to the address change. t_{WR} applied in case a write ends as $\overline{CS}$ or $\overline{WE}$ going high.
6. If $\overline{OE}$, $\overline{CS}$ and $\overline{WE}$ are in the Read Mode during this period, the I/O pins are in the output low-Z state. Inputs of opposite phase of the output must not be applied because bus contention can occur.
7. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.
8. If $\overline{CS}$ goes low simultaneously with $\overline{WE}$ going or after $\overline{WE}$ going low, the outputs remain high impedance state.
9. Dout is the read data of the new address.
10. When $\overline{CS}$ is low : I/O pins are in the output state. The input signals in the opposite phase leading to the output should not be applied.

FUNCTIONAL DESCRIPTION

$\overline{CS}$	$\overline{WE}$	$\overline{OE}$	Mode	I/O Pin	Supply Current
H	X	X*	Not Select	High-Z	I_{SB}, I_{SB1}
L	H	H	Output Disable	High-Z	I_{CC}
L	H	L	Read	D_{OUT}	I_{CC}
L	L	X	Write	D_{IN}	I_{CC}

* X means Don't Care.

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PACKAGE DIMENSIONS

32-SOJ-400

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